



WBFBP-03B Plastic-Encapsulate Diodes

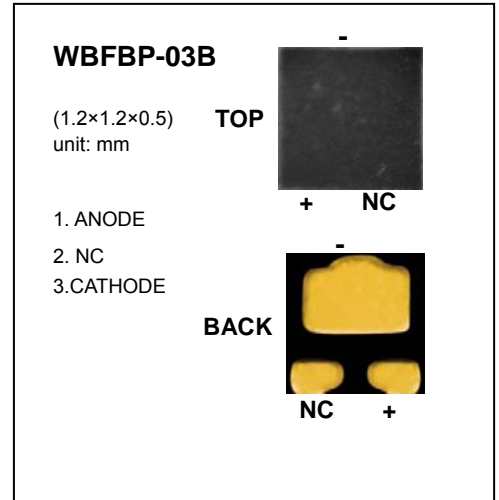
DS54NND03 SCHOTTKY BARRIER DIODE

DESCRIPTION

- Epitaxial Planar Silicon Diode

FEATURES

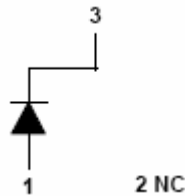
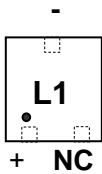
- Ultra-Small Surface Mount Package
- Low Forward Voltage Drop
- Fast Switching
- PN Junction Guard Ring for Transient and ESD Protection
- Available in Lead Free Version



APPLICATION

Ultra High Speed Switching
 For Portable Equipment:(i.e. Mobile Phone,MP3, MD,CD-ROM, DVD-ROM, Note Book PC, etc.)

MARKING: L1



Maximum Ratings @Ta=25°C

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	30	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
Forward Continuous Current (Note 1)	I_{FM}	200	mA
Repetitive Peak Forward Current	I_{FRM}	300	mA
Forward Surge Current @ $t < 1.0s$	I_{FSM}	600	mA
Power Dissipation (Note 1)	P_d	150	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	667	°C/W
Junction Temperature	T_J	125	°C
Storage Temperature Range	T_{STG}	-55~+150	°C

Notes 1: Device mounted on FR-4 PC board with recommended pad layout

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	30		V
Reverse leakage current	I_R	$V_R=25V$		2	μA
Forward voltage	V_F	$I_F=0.1mA$ $I_F=1mA$ $I_F=10mA$ $I_F=30mA$ $I_F=100mA$		240 320 400 500 1000	mV
Total capacitance	C_T	$V_R=1V, f=1MHz$		10	pF
Reverse recovery time	t_{rr}	$I_F=10mA, I_R=1mA\sim 10mA$ $R_L=100\Omega$		5	ns